

**SANYO**

No.2124A

**DS462**

Silicon Epitaxial Planar Type

High-Voltage Switching Diode

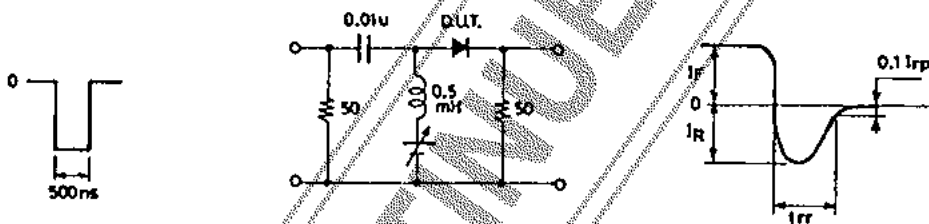
**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Condition	Value	Unit
Peak Reverse Voltage	$V_{RM}$		-250	V
Reverse Voltage	$V_R$		-200	V
Peak Forward Current	$I_{FM}$		600	mA
Average Rectified Current	$I_O$		200	mA
Surge Forward Current	$I_{FSM}$	10msec pulse	2000	mA
Allowable Power Dissipation	P		400	mW
Junction Temperature	$T_j$		175	°C
Storage Temperature	$T_{stg}$		-65 to +175	°C

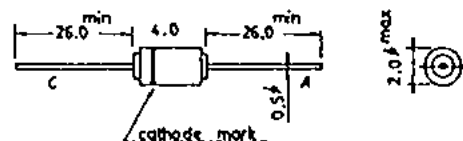
**Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Condition	min	typ	max	Unit
Forward Voltage	$V_{F1}$	$I_F = 1\text{mA}$			0.8	V
	$V_{F2}$	$I_F = 100\text{mA}$	0.95		1.2	V
Reverse Current	$I_R$	$V_R = -200\text{V}$			-0.5	μA
Interterminal Capacitance	c	$V_R = 0\text{V}, f = 1\text{MHz}$		1.0		pF
Reverse Recovery Time	$t_{rr}$	$I_F = I_R = 10\text{mA}, R_L = 50\Omega$			60	ns

**Reverse Recovery Time Test Circuit**



**Case Outline 1080 (unit: mm)**

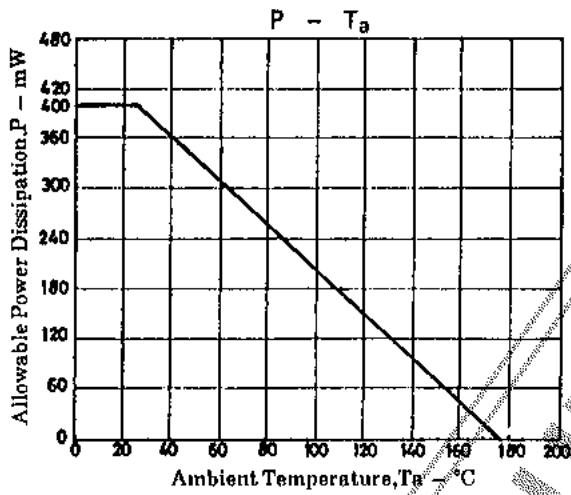
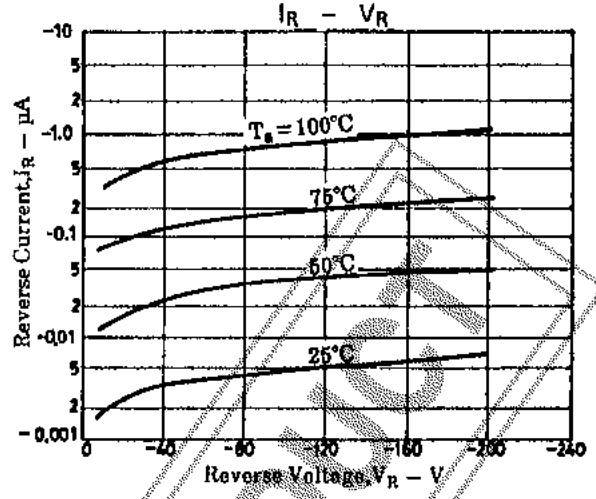
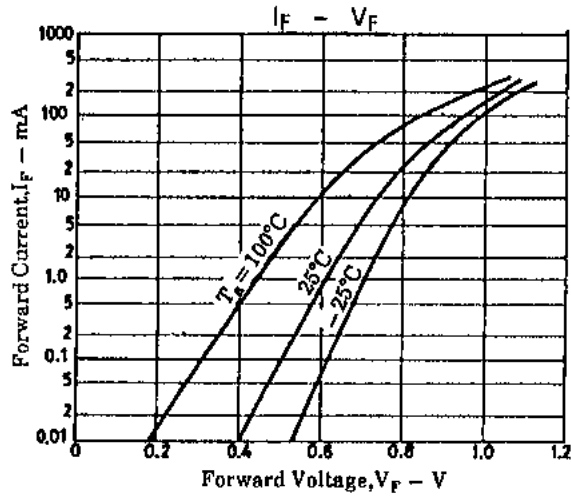


C: Cathode  
A: Anode

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use, nor for any infringements of patents or other rights of third parties which may result from its use.

Specifications and information herein are subject to change without notice.

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DISCONTINUED PRODUCT